



**HiPerFET™
Power MOSFETs
Q Class**

**IXFH 13N80Q
IXFT 13N80Q**

V_{DSS} = 800 V
I_{D25} = 13 A
R_{DS(on)} = 0.70 Ω
t_{rr} ≤ 250 ns

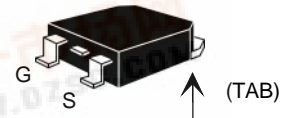
N-Channel Enhancement Mode
Avalanche Rated High dv/dt, Low Q_g

Preliminary data sheet

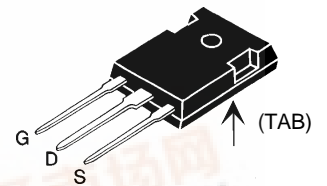


Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	800	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	800	V
V _{GS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	13	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	52	A
I _{AR}	T _C = 25°C	13	A
E _{AR}	T _C = 25°C	28	mJ
E _{AS}	T _C = 25°C	750	mJ
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	5	V/ns
P _D	T _C = 25°C	250	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C
M _d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-268 (D3) (IXFT) Case Style



TO-247 AD (IXFH)



G = Gate D = Drain
S = Source TAB = Drain

Features

- IXYS advanced low Q_g process
- International standard packages
- Low R_{DS(on)}
- Unclamped Inductive Switching (UIS) rated
- Fast switching
- Molding epoxies meet UL94 V-0 flammability classification

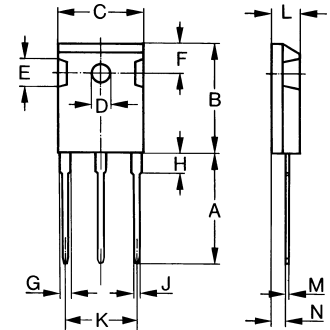
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	800		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 4 mA	2.5		V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0 V	T _J = 25°C		50 μA
		T _J = 125°C		1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			0.70 Ω



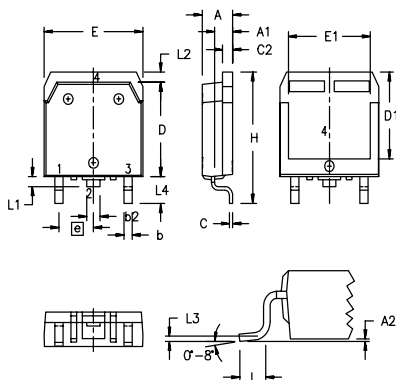
Symbol	Test Conditions	Characteristic Values		
		(T _j = 25°C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} pulse test	8	13	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		3250	pF
C_{oss}			310	pF
C_{rss}			60	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 3.2 Ω (External)		23	ns
t_r			36	ns
t_{d(off)}			55	ns
t_f			19	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		90	nC
Q_{gs}			20	nC
Q_{gd}			30	nC
R_{thJC}	(TO-247)			0.42 K/W
R_{thCK}			0.25	K/W

TO-247 AD (IXFH) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Source-Drain Diode
Characteristic Values
(T_j = 25°C, unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			13 A
I_{SM}	Repetitive;			52 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = I _S , -di/dt = 100 A/μs, V _R = 100 V			250 ns
Q_{RM}			0.8	μC
I_{RM}			7.5	A

TO-268AA (D³ PAK)


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L ₁	1.20	1.40	.047	.055
L ₂	1.00	1.15	.039	.045
L ₃	0.25 BSC		.010 BSC	
L ₄	3.80	4.10	.150	.161

Min. Recommended Footprint
